2SB1121

Bipolar Transistor -25V, -2A, Low VCE(sat) PNP Single PCP



Applications

• Voltage regulators, relay drivers, lamp drivers, electrical equipment

Features

- Adoption of FBET, MBIT processes
- Large current capacity and wide SOA
- Low collector to emitter saturation voltage • Fast switching speed
- Ultrasmall size making it easy to provide high-density, small-sized hybrid IC's

Specifications

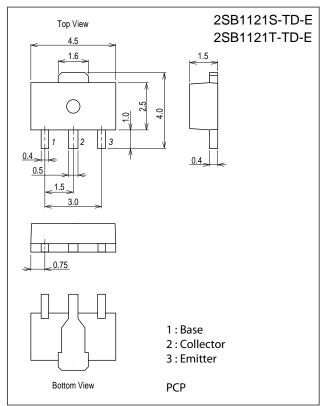
Absolute Maximum Ratings at $Ta = 25^{\circ}C$

| 0 | | | | |
|------------------------------|--------|------------|---------|------|
| Parameter | Symbol | Conditions | Ratings | Unit |
| Collector to Base Voltage | VCBO | | -30 | V |
| Collector to Emitter Voltage | VCEO | | -25 | V |
| Emitter to Base Voltage | VEBO | | -6 | V |
| Collector Current | IC | | -2 | А |
| Collector Current (Pulse) | ICP | | -5 | А |

Continued on next page.

Package Dimensions

unit : mm (typ) 7007B-004



Product & Package Information

• Package

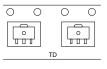
• JEITA, JEDEC

- - : SC-62, SOT-89, TO-243

Marking

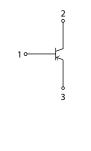
• Minimum Packing Quantity : 1,000 pcs./reel

Packing Type: TD





Electrical Connection



: PCP

Continued from preceding page.

| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------|--------|---|-------------|------|
| Collector Dissipation | PC | | 500 | mW |
| | | When mounted on ceramic substrate (250mm ² ×0.8mm) | 1.3 | W |
| Junction Temperature | Тј | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

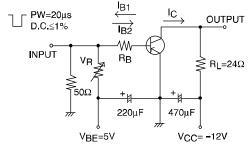
Electrical Characteristics at $Ta = 25^{\circ}C$

| Parameter | Symbol | | | Ratings | | |
|---|-----------------------|---|------|---------|------|------|
| | | Conditions | min | typ | max | Unit |
| Collector Cutoff Current | ICBO | V _{CB} =-20V, I _E =0A | | | -0.1 | μΑ |
| Emitter Cutoff Current | IEBO | V _{EB} =-4V, I _C =0A | | | -0.1 | μΑ |
| DC Current Gain | hFE1 | V _{CE} =-2V, I _C =-100mA | 140* | | 400* | |
| | hFE2 | V _{CE} =-2V, I _C =-1.5A | 65 | | | |
| Gain-Bandwidth Product | fΤ | V _{CE} =-10V, I _C =-50mA | | 150 | | MHz |
| Output Capacitance | Cob | V _{CB} =-10V, f=1MHz | | 32 | | pF |
| Collector to Emitter Saturation Voltage | V _{CE} (sat) | IC=-1.5A, IB=-75mA | | -0.35 | -0.6 | V |
| Base to Emitter Saturation Voltage | V _{BE} (sat) | IC=-1.5A, IB=-75mA | | -0.85 | -1.2 | V |
| Collector to Base Breakdown Voltage | V(BR)CBO | I _C =-10μA, I _E =0A -30 | | | | V |
| Collector to Emitter Breakdown Voltage | V(BR)CEO | I _C =-1mA, R _{BE} =∞ | -25 | | | V |
| Emitter to Base Breakdown Voltage | V(BR)EBO | I _E =-10μΑ, I _C =0Α | -6 | | | V |
| Turn-ON Time | ton | | | 60 | | ns |
| Storage Time | tstg | See specified Test Circuit | | 350 | | ns |
| Fall Time | tf | 1 | | 25 | | ns |

*: The 2SB1121 is classified by 100mA hFE as follows:

| Rank | S | Т |
|-----------------|------------|------------|
| h _{FE} | 140 to 280 | 200 to 400 |

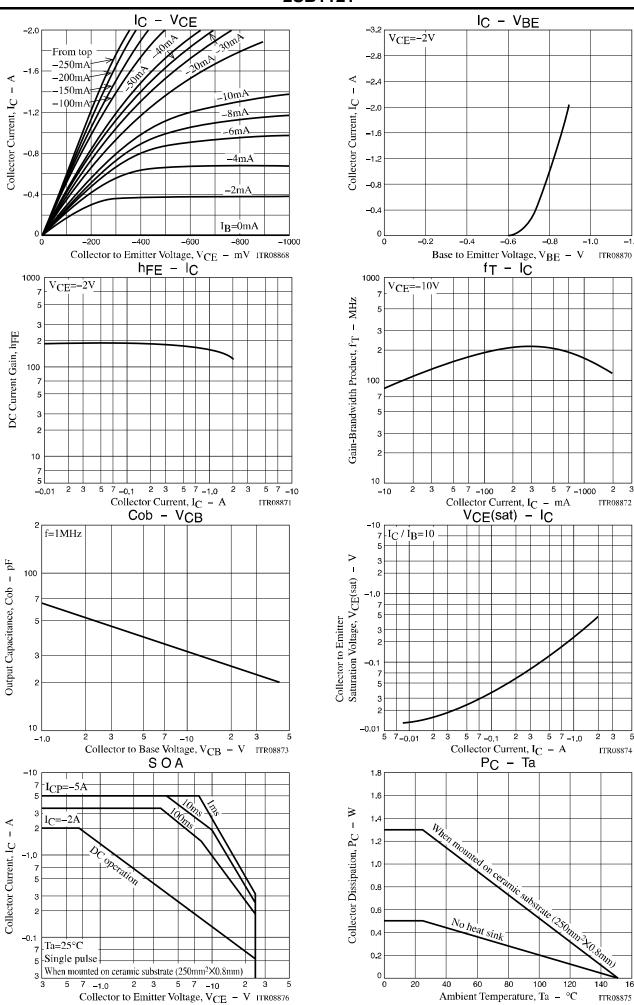
Switching Time Test Circuit



 $I_{C}=20I_{B1}=-20I_{B2}=-0.5A$

Ordering Information

| Device | Package | Shipping | Memo |
|--------------------------------|---------|----------------|---------|
| 2SB1121S-TD-E 2SB1121T-TD-E | PCP | 1,000pcs./reel | Pb-Free |



ITR08875

160

140

-1.2

2 3

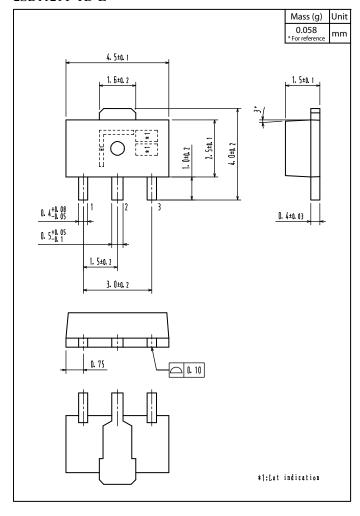
ITR08872

2 3 5

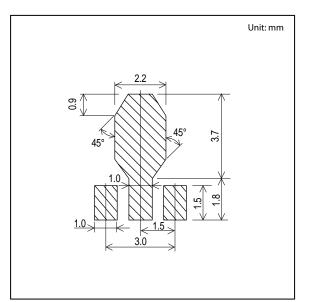
ITR08874

Outline Drawing

2SB1121S-TD-E 2SB1121T-TD-E



Land Pattern Example



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